TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

S6903G,S6903J

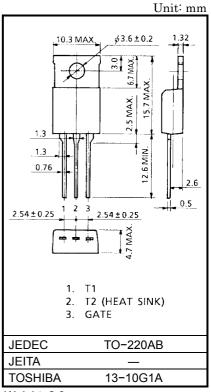
AC POWER CONTROL APPLICATIONS

High Rush Current Capability
 Optimal for controlling actuators where high rush current may flow.
 ITRM = 120A (n = 100k cycle, Tc = 45°C)

R.M.S On-State Current : IT (RMS) = 20A
 Repetitive Peak Off-State Voltage : VDRM = 400V, 600V

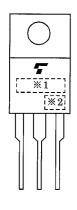
MAXIMUM RATINGS

| CHARACTERI | STIC | SYMBOL | RATING | UNIT | |
|---|-------------------------|----------------------|-------------------------|------------------|--|
| Repetitive Peak Off-State Voltage | S6903G | \/ | 400 | V | |
| | S6903J | V_{DRM} | 600 | | |
| R.M.S On-State Current (Full Sine Waveform Tc | • | I _{T (RMS)} | I _{T (RMS)} 20 | | |
| Peak One Cycle Surge On-State Current (Non-Repetitive) | | l | 180 (50Hz) | Α | |
| | | ITSM | 200 (60Hz) | | |
| Repetitive Surge On-Sta | ate Current (Note 1) | I _{TRM} | 120 | А | |
| I ² t Limit Value | | 1 ² t | 167 | A ² s | |
| Critical Rate of Rise of On-State Current | | di / dt | 50 | A / μs | |
| Peak Gate Power Dissip | ation | P_{GM} | 5 | W | |
| Average Gate Power Dissipation | | P _{G (AV)} | 0.5 | W | |
| Peak Gate Voltage | | V_{GM} | 10 | V | |
| Peak Gate Current | | I_{GM} | 2 | Α | |
| Junction Temperature | | Tj | T _j -40~125 | | |
| Storage Temperature Ra | T _{stg} | -40~125 | °C | | |



Weight: 2.0 g

MARKING



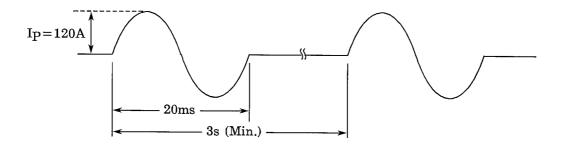
| NUMBER | SYMBO | MARK | | |
|--------|--|---|---|--|
| *1 | TYPE - | S6903G | S6903G | |
| | | S6903J | S6903J | |
| *2 | Lot Number Month (Star Alph Year (Last I of the | ting from nabet A Decimal Digit Current Year | Example 8A: January 1998 8B: February 1998 8L: December 1998 | |



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | TEST CONDITION | | MIN | TYP. | MAX | UNIT |
|---|-----|------------------------|--|------------------|-----|------|-----|-------|
| Repetitive Peak Off-State Current | | I _{DRM} | V _{DRM} = Rated | | _ | _ | 20 | μA |
| Gate Trigger Voltage | I | - V _{GT} | V _D = 12V R _L = 20Ω | T2 (+), Gate (+) | _ | _ | 1.5 | V |
| | II | | | T2 (+), Gate (-) | _ | _ | 1.5 | |
| | III | | | T2 (-), Gate (-) | _ | _ | 1.5 | |
| | IV | | | T2 (-), Gate (+) | _ | _ | _ | |
| Gate Trigger Current | I | l _{GT} | V _D = 12V R _L = 20Ω | T2 (+), Gate (+) | _ | _ | 30 | - mA |
| | II | | | T2 (+), Gate (-) | _ | _ | 30 | |
| | III | | | T2 (-), Gate (-) | _ | _ | 30 | |
| | IV | | | T2 (-), Gate (+) | _ | _ | _ | |
| Peak On-State Voltage | | V _{TM} | I _{TM} = 30A | | _ | _ | 1.6 | V |
| Gate Non-Trigger Voltage | | V _{GD} | V _D = Rated, Tc = 125°C | | 0.2 | _ | _ | V |
| Holding Current | | lΗ | V _D = 12V, I _{TM} = 2A | | _ | _ | 50 | mA |
| Thermal Resistance R _{th} | | R _{th (j-c)} | Junction to Case, AC | | _ | _ | 1.0 | °C/W |
| Critical Rate of Rise of Off-State Voltage at Commutation | | (dv / dt) _c | $V_{DRM} = 400V, T_j = 125^{\circ}C$ (di / dt) c = -8.7Å / ms | | 10 | _ | _ | V /µs |

Note 1: Repetitive Surge On-State Current



 I_P = 120A (f = 50Hz) at Tc = 45°C

Max. Repetitive Number of cycle n = 100k cycle (Repetitive cycle T = 3s Min.)

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